Selective and Facile C-F Bond Activation of Trifluoromethyl Groups on Cu(111)

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Activation of the strongest bond that carbon can form, the C-F bond, remains a topic of recent interest.¹ It has long been known that interaction of fluorocarbons with a metal center may ultimately lead to the cleavage of such robust bonds. Catalytic activation of C-F bonds by metal complexes in solution is the subject of several reviews.^{2,3} Trifluoromethyl transition-metal complexes draw our particular attention because M-CF₃ species have been recognized as precursors to M=CF₂ (difluorocarbene) complexes.⁴ We are interested in such problems regarding controlled C-F activation of small fluorocarbons bound to metal surfaces. The chemistry of trifluoromethyl groups adsorbed on metal single-crystal surfaces was explored by the reactions of trifluoromethyl iodide (CF₃I) with Ni, $^{5-7}$ Ru, 8,9 Pt^{10,11}, and Ag.¹² Except for silver (CF₃ desorbs as a radical), experimental results revealed that the C-F bonds could be ruptured, however, in either uncontrolled fashion or at high temperatures. Removal of a single fluorine atom from the CF₃ fragment could not be achieved with high selectivity, as displayed for metal complexes.

We speculate that the choice of metal surfaces might be pivotal. Here we report a novel C-F activation in chemisorbed CF₃ moieties using a Cu(111) surface. The key findings of this work are 2-fold: First, only one C-F bond in the trifluoromethyl is broken, suggesting *selective activation* of carbon-fluorine bonds rather than complete defluorination, and the formation of a difluorocarbene intermediate on the surface. Without other competing reaction channels, all the CF3 groups undergo this mild C-F decomposition pathway at and below the monolayer coverage. Second, C-F bonds are cleaved by the copper surface below 160 K. This low reaction temperature can be translated, in kinetics terms, into small activation energy; therefore, remarkably *facile* bond activation is implied.

The experiments were performed in an ultrahigh vacuum chamber described in detail elsewhere.13 In brief, the system is equipped with an ion sputtering gun and a retarding-field analyzer for both Auger electron spectroscopy and low-energy electron diffraction. A quadrupole mass spectrometer is shielded in a differentially pumped cylindrical cage assembly with an aperture

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Cu(111) / 1.25L CF₃I Adsorption (stio 250K (arb. I TPD/R Peak fon Intensity (arb. units) 0.0 0.5 1.0 1.5 Coverage of CF, 1.5 (CF)m = 3*m/e*=50 (CF_2^+) (CF_{3}^{+}) m/e=69 $(C_{7}F_{7}^{+})$ m/e=81 $(C2F_{4}^{+})$ m/e=100 $(C_2F_5^+)$ m/e=119 (CF₃I⁻) m/e=196 300 100 200 400 500 600 Surface Temperature (K)

Figure 1. Multiple-ion TPR/D spectra of m/e 31 (CF⁺), 50 (CF₂⁺), 69 (CF_3^+) , 81 $(C_2F_3^+)$, 100 $(C_2F_4^+)$, 119 $(C_2F_5^+)$, and 196 (CF_3I^+) after the adsorption of 1.25 L of CF₃I on Cu(111) at 110 K. Ions were monitored with the mass spectrometer ionizer energy set at 70 eV. The heating rate was 2 deg K/s. It should be noted that the current levels on the Cu(111) were less than 1 nA with our experimental configurations; therefore, the desorption features were surely not stimulated by electrons emitted from the ion source of the mass spectrometer. The inset shows the integrated peak areas, calculated from m/e 81 (tetrafluoroethylene formation) and 196 (molecular desorption) TPR/D features, as a function of CF₃I exposure.

of 2 mm diameter to conduct temperature-programmed reaction/ desorption (TPR/D) studies. CF₃I has been widely used as a source of adsorbed CF3 moieties on a variety of metal surfaces5-12 because the C-I bond is weak, and is known to break readily upon adsorption, yielding the desired CF₃ species. As illustrated in Figure 1, multiple-ion TPR/D survey shows a featureless trace of *m/e* 196 following the adsorption of 1.25 L (1 L = 10^{-6} Torr s) of CF₃I at 110 K. This observation indicates no molecular desorption occurs from the surface at this exposure, suggesting that all the adsorbed CF₃I undergo C-I bond scission. Because the ion signals of CF_3^+ (*m/e* 69) and $C_2F_5^+$ (*m/e* 119) are also absent, the possibility of forming the CF₃ free radical, perfluoromethane, and perfluoroethane can be ruled out. The only desorption state is featured by m/e 31 (CF⁺), 50 (CF₂⁺), 81 $(C_2F_3^+)$, and 100 $(C_2F_4^+)$ with peak maxima at 250 K. The relative ion abundance of these desorption profiles nearly duplicates the fragmentation pattern of tetrafluoroethylene (CF2=CF2).14 Intuitively, coupling of two difluorocarbene (CF₂) units would afford tetrafluoroethylene. The intermediacy of a surface-bound difluo*rocarbene*, $CF_{2(ad)}$, can be invoked to account for the observed product. The lack of 'CF₃, CF₄ ,and C₂F₆ suggests complete conversion from CF_{3(ad)} to CF_{2(ad)}. CF_{2(ad)} restricts itself from being further decomposed into CF(ad) and carbidic carbon because the Auger data reveal the disappearance of carbon signal above 250 K, which coincides with the desorption of $CF_2=CF_2$. The fate of fluorine atoms on the surface, resulting from the selective C-F bond activation $CF_{3(ad)} \rightarrow CF_{2(ad)} + F_{(ad)}$, eventually leads to etching of the substrate by evolving CuF in the gas phase above 700 K (TPR/D data are not shown here). Surface-bound iodine due to the initial C-I bond dissociation ultimately desorbs as iodine atoms in a broad temperature range from 600 to 900 K.

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Figure 2. TPR/D spectra of three different types of ethylene due to competing carbene coupling reactions after exposing the Cu(111) surface, which was preadsorbed with 0.15 L of CF₃I, to an *X* amount of CD₂I₂ (X = 0, 0.5, 1, 2, 3 L exposures). The representative ions are *m/e* 32 (CD₂=CD₂⁺, left), 66 (CF₂=CD₂⁺, middle), and 100 (CF₂=CF₂⁺, right), respectively. It should be noted that the tiny feature at 158 K in all the CF₂=CF₂ (*m/e* 100) spectra resulted from traces of tetrafluoroethylene impurity in the CF₃I gas manifold.

The reaction scheme described above holds for all the CF₃I exposures below 1.25 L. Due to active-site availability, intact molecular desorption starts to compete with tetrafluroethylene formation in the TPR/D spectra at higher doses. As shown in the inset of Figure 1, according to the uptake curves of $C_2F_3^+$ (*m*/*e* 81) and CF₃I⁺ (*m*/*e* 196), it is reasonable to assign 1.25 L to the saturation coverage of one monolayer (ML) of CF₃I.

The intermediacy of $CF_{2(ad)}$ deserves further scrutiny. We can verify this intermediate state based upon purely chemical evidence. Our approach, borrowed from the concept of "carbene scavengers", utilizes a labeled substance that is added to the surface to counteract the self-coupling of CF_{2(ad)} (if any) and meanwhile to remove difluorocarbene as an easily identifiable species. Here this substance is chosen to be deuterium-labeled diiodomethane (CD₂I₂), a well-known precursor for generating surface methylene. The chemistry of CD₂I₂ on Cu surfaces studied by Chiang et al.¹⁵ reveals facile dissociation of C-I bonds to form CD_{2(ad)} followed by methylene recombination, yielding CD₂=CD₂ as the sole gasphase product. Figure 2 juxtaposes the TPR/D spectra of three different types of ethylene, CF₂=CF₂ (m/e 100, right panel), CF₂= CD_2 (*m/e* 66, middle panel), and $CD_2=CD_2$ (*m/e* 32, left panel), in a series of experiments by adding various amounts of CD₂I₂ (scavengers) on Cu(111) which was preadsorbed by 0.15 L of $CF_{3}I$ (~1/10 ML). These data demonstrate that the formation of CF₂=CF₂ (250 K), originating from CF_{3(ad)}, is being suppressed and finally blocked entirely as a function of increasing $CD_{2(ad)}$. Concomitantly, yields of CD2=CD2 from recombination of CD2(ad) at 160 K are found to increase. The most informative results consist of the emerging $CF_2=CD_2$, which is responsible for the descending yields of CF2=CF2. This cross-coupling product

ensures the presence of surface difluorocarbene, which imperatively demands that C-F bond cleavage proceed in a selective fashion. Furthermore, the 163 K liberation of CF₂=CD₂ reflects that the C-F bond in CF₃ has already been activated *prior to* or *at* this temperature. That CF₂=CF₂ formed at 250 K is thus rate limited by the CF₂ coupling step instead of C-F activation. It is apparent that the addition of scavengers helps to place the kinetic upper limit for the C-F activation more accurately by 90 K (163 vs 250 K). In summary, we propose the following mechanism to delineate the aforementioned events and relevant kinetic information:



The role of Cu(111), the substrate used in this study, merits comment. The catalytic activity of atomically clean copper surfaces under ultrahigh vacuum (UHV) conditions can be classified into two categories. The first encompasses dehydrogenation reactions, such as α - and β -elimination in alkyl groups.¹⁶ Methyl (CH₃) is stable on the copper surface until approximately 450 K, where a number of competing reactions occur, including α -hydrogen elimination to yield a methylene (CH₂) intermediate. Therefore, a similar reactivity toward CF₃ is somewhat expected; however, the extremely low temperature for the C–F activation and the total domination of this reaction route are unusual. The second category is associated with the facile C–C coupling reactions to evolve alkanes^{17,18} and alkenes.^{17,19} This reactivity becomes a mechanistic probe that allows us to approach the kinetic limit for the C–F bond activation as exact as possible.

Activation of saturated C–F bonds has been investigated by trifluoromethyl groups chemisorbed on Cu(111). To our knowledge, this is the first example capable of readily and selectively cleaving a single C–F bond to transform CF₃ into CF₂ moieties on a well-defined metallic surface under UHV ambiences. In perspective, this discovery provides a convenient method for generating difluorocarbene intermediates. A variety of surface reactions involving carbenes, such as abstraction, addition, and insertion, can be studied and compared with its hydrocarbon counterpart, methylene, to give insight into the effects of fluorination on reactivity.

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